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SwissSEM China

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PACIFIC SEMICONDUCTOR TECHNOLOGY (ZHEJIANG) CO., LTD

Group Introduction

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SUN.KING TECHNOLOGY GROUP LIMITED
赛晶科技集團有限公司

Founded in 2002

Listed on the Hong Kong Main Board, stock code 580. HK

The business is oriented to the whole new energy industry chain

In particular, wind power, photovoltaic, DC transmission, electric vehicles, energy storage, industrial control, ships, railways, etc.

It has more than 10 subsidiaries in China and Europe

1100+
Total number of employees

30%+
Proportion of technical R&D personnel

280+item
Patent certificate

20+item
Provincial and municipal innovation honors

5item
National energy technology achievement certification

Group distribution

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SwissSEM China

Beijing Group Headquarters

Wuhan, Hubei

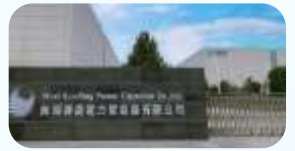
Wuhan Langde Electric Co., Ltd

Othmarsingen, Switzerland

Astrol Electronlc AG
SwissSEM Technologies AG

Wuxi, Jiangsu

Wuxi Saijing Power Capacitor Co., Ltd



Hamburg, Germany

morEnergy GmbH

Jiashan, Zhejiang

Jiashan Huarui SwissSEM China Electrical Equipment Technology Co., Ltd
SwissSEM China Pacific Semiconductor Technology (Zhejiang) Co., Ltd
Jiashan SwissSEM China Capacitor Co., Ltd
Zhejiang Saiying Electric Power Technology Co., Ltd
Zhejiang Jiashan Keneng Power Equipment Co., Ltd
SwissSEM China New Energy Technology Co., Ltd

Rotterdam, Netherlands

Astrolkwx B.V.

Ningbo, Zhejiang

Ningbo Hairong Electric Appliance Co., Ltd

Core components of the new energy industry chain

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New energy power generation

Self-developed SiC and IGBT chips and modules

Cascading busbar

Integrated busbar

New energy Large-scale grid connection and long-distance delivery

anodic saturation reactor

Power electronics capacitors

Cascading busbar

High-power IGBTs

Power capacitors

New energy electricity

Self-developed SiC and IGBT chips and modules

Cascading busbar

Integrated busbar

Innovative Technology - Serving the New Power System

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Smart grid online monitoring

- It is one of the key technologies for the intelligent development of power grids, covering all aspects of power systems such as transmission, distribution, and substation
- Greatly improve the level of intelligent management, improve the safety and stability of power grid operation, and reduce operation and maintenance costs
- It has achieved outstanding results in more than ten domestic UHV DC transmission and smart grid scientific research demonstration projects, as well as overseas projects such as Russia, Israel, and Bangladesh

Solid-state pulse switch

- The most internationally authoritative technical expert teams with over 20 years of technical accumulation possess globally leading technological capabilities.
- **Representative Cases:**

•Nuclear fusion research by multiple U.S. companies
•The positron-electron collider project at the Institute of High Energy Physics (IHEP), Chinese Academy of Sciences
•The high-voltage laboratory at ETH Zurich (Swiss Federal Institute of Technology)
•The U.S. Electric Fish Barrier Project

Innovative Technology - Serving the New Power System

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Solid-state pulse switches

- Microsecond switching speed, intelligent and modular design
- Norwegian Classification Society certification
  - China Classification Society certification
  - Siemens supplier in the marine sector
- **Typical Cases:**
  - China's Zhuhai cloud intelligent mothership
  - China offshore wind operation and maintenance mother ship
  - A railway scientific research project in China
  - European offshore wind power installation vessel
  - UK Smart Grid Demonstration Project
  - European CERN Particle Collider

In-line real-time impedance measurement

- Innovative technology with international invention patents realizes online and real-time impedance data measurement
- It is of great value to new energy power generation, charging, energy storage and other power distribution systems
- Outstanding performance in the fields of wind and photovoltaic power plants, electrified ships, car charging stations, electrified railway vehicles, and inverter elevators in Europe

Flexible AC transmission units

- The comprehensive solution of AC transmission technology FACTS includes: SVC, SVG, DC ice melting device, low-voltage ride-through device and other products
- It has made many outstanding achievements in the fields of electrified railways, new energy power plants, metallurgy, and industrial control

About us

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PACIFIC SEMICONDUCTOR TECHNOLOGY(ZHEJIANG) CO., LTD

SwissSEM Semiconductor possesses domestically scarce and internationally leading independent chip technology

Chip products

Fine trench gate technology

Micro trench gate technology

SiC technology

- **IGBT Product coverage**
  1050V 1200V 1700V
- **SiC The product voltage range covers**
  650V 750V 1200V 1700V 2000V
- **Low voltage MOS has a rich product line**
  ComplementaryN+P Dual NMOS SGT LVMOS SJ MOS Trench LVMOS

Company Business

A high-tech enterprise specializing in the research and manufacturing of high-end power semiconductor products such as IGBT, FRD, and silicon carbide chips and modules;

Corporate Vision

Committed to promoting the development of energy towards a more sustainable and green direction, and promoting the transformation of traditional fossil fuels into green electricity.

About us

R&D Center

Located in Othmarsingen, Switzerland

The technical research and development team is composed of top experts in IGBT and SiC design and manufacturing from Europe and China, as well as industry leaders with excellent performance and decades of practical experience in the field of power semiconductors.

Manufacturing Center

Located in Jiashan County, Zhejiang Province, China

The first phase of the manufacturing center project covers an area of 22000 square meters, and the second phase project covers an area of 50000 square meters. It plans to construct multiple fully automatic intelligent IGBT and SiC production lines with international first-class level, as well as a domestic technology center.

Module Products

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◆ ST —IGBT

- 1200V/200A • 1200V/250A • 1200V/300A • 1200V/450A • 1200V/600A • 1200V/800A
- 1700V/200A • 1700V/300A • 1700V/450A • 1700V/600A

◆ ED —IGBT

- 1200V/450A • 1200V/600A • 1200V/750A • 1200V/900A
- 1700V/450A • 1700V/600A • 1700V/900A

◆ BEVD —IGBT

- 1200V/400A
- 1200V/500A

◆ EP —IGBT

- 1700V/75A • 1700V/100A • 1700V/150A
- 1700V/200A

◆ EVD —IGBT/SiC

- 1200V/600A • 1200V/ 2mΩ • 1200V/ 3mΩ
- 1200V/ 4mΩ

◆ TF —IGBT

- 1700V/75A • 1700V/ 100A
- 1700V/ 150A

◆ FP —IGBT

- 1050V/650A

◆ HEEV —SiC

- 1200V/ 2mΩ • 1200V/ 3mΩ
- 1200V/ 4mΩ

IGBT model Roadmap

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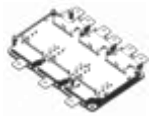
IGBT products	Specification	Lead time for samples	Mass production lead time
XP model 	2300V 1400A	July 2026	December 2026
ST model 	1200V 1000A	March 2026	July 2026
EP model 	1200V 75A/100A/150A	September 2026	TBD
FP model 	1400V 600A	June 2026	TBD
EVD model 	1200V 2mΩ/3mΩ/4mΩ	February 2026	August 2026
	1200V 600A	February 2026	August 2026

Discrete Device Products

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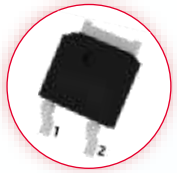


TO-252-2L SiC SBD

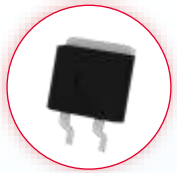
- 650V/4A
- 650V/6A
- 650V/8A
- 650V/10A
- 650V/16A
- 650V/20A
- 650V/30A
- 1200V/2A
- 1200V/3A
- 1200V/5A
- 1200V/10A
- 1200V/15A

TO-220-2L SiC SBD

- 650V/4A
- 650V/6A
- 650V/8A
- 650V/10A
- 650V/16A
- 650V/20A
- 1200V/2A
- 1200V/3A
- 1200V/5A
- 1200V/10A
- 1200V/15A
- 1200V/20A

SMBF —SiC SBD

- 650V/1A
- 1200V/1A
- 1200V/2A
- 1200V/3A

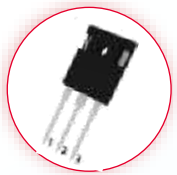


TO-263-2L SiC SBD

- 650V/8A
- 650V/10A
- 650V/20A
- 650V/30A
- 650V/40A
- 650V/50A
- 1200V/ 10A
- 1200V/20A

TO-247-2L SiC SBD

- 650V/8A
- 650V/16A
- 650V/20A
- 650V/30A
- 650V/40A
- 650V/50A
- 1200V/15A
- 1200V/20A
- 1200V/30A
- 1200V/40A
- 1200V/50A
- 1200V/60A
- 1700V/50A
- 1700V/5A
- 1700V/25A
- 2000V/40A
- 2000V/20A



TO-247-3L SiC SBD

- 650V/16A
- 650V/20A
- 650V/30A
- 650V/40A
- 650V/60A
- 1200V/10A
- 1200V/ 20A
- 1200V/30A
- 1200V/40A
- 1200V/60A

Discrete Device Products

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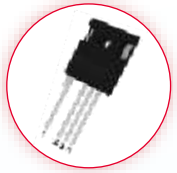
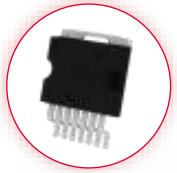


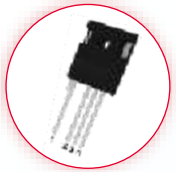
TO-247-4L SiC MOSFET

- 650V/18mΩ
- 650V/27mΩ
- 650V/35mΩ
- 650V/50mΩ
- 650V/65mΩ
- 750V/9mΩ
- 750V/7mΩ
- 1200V/13mΩ
- 1200V/14mΩ
- 1200V/20mΩ
- 1200V/32mΩ
- 1200V/ 40mΩ
- 1200V/ 60mΩ
- 1200V/75mΩ
- 1200V/120mΩ
- 1400V/20mΩ
- 1400V/32mΩ



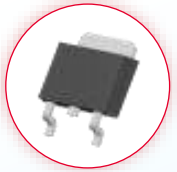
TO-263-7L SiC MOSFET

- 650V/ 18mΩ
- 650V/ 27mΩ
- 650V/ 35mΩ
- 650V/ 50mΩ
- 650V/ 65mΩ
- 1200V/ 32mΩ
- 1200V/ 40mΩ
- 1200V/ 60mΩ
- 1200V/ 75mΩ
- 1200V/ 120mΩ
- 1700V/ 1Ω



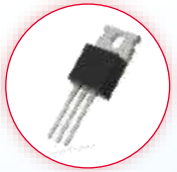
TO-247-3L SiC MOSFET

- 650V/ 18mΩ
- 650V/ 27mΩ
- 650V/ 35mΩ
- 650V/ 50mΩ
- 1200V/ 32mΩ
- 1200V/ 40mΩ
- 1200V/ 75mΩ
- 1700V/ 1Ω



TO-252-2L SiC MOSFET

- 650V/ 200mΩ



TO-220-3L SiC MOSFET

- 1200V/ 60mΩ
- 1200V/ 50mΩ

LVMOSFET Product Catalog

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Mass Production

◆ SGT MOS

- G3

30V 60V 100V 40V 80V

- G2

30V 60V 100V 40V 80V

120V 150V 200V

◆ Trench MOS

40V 80V 100V 60V 30V

12~20V

2025

Under Developing

◆ SGT MOS

- G3

120V 150V 200V

- G2

250V

- G4

30V 60V 40V

LVMOSFET product series

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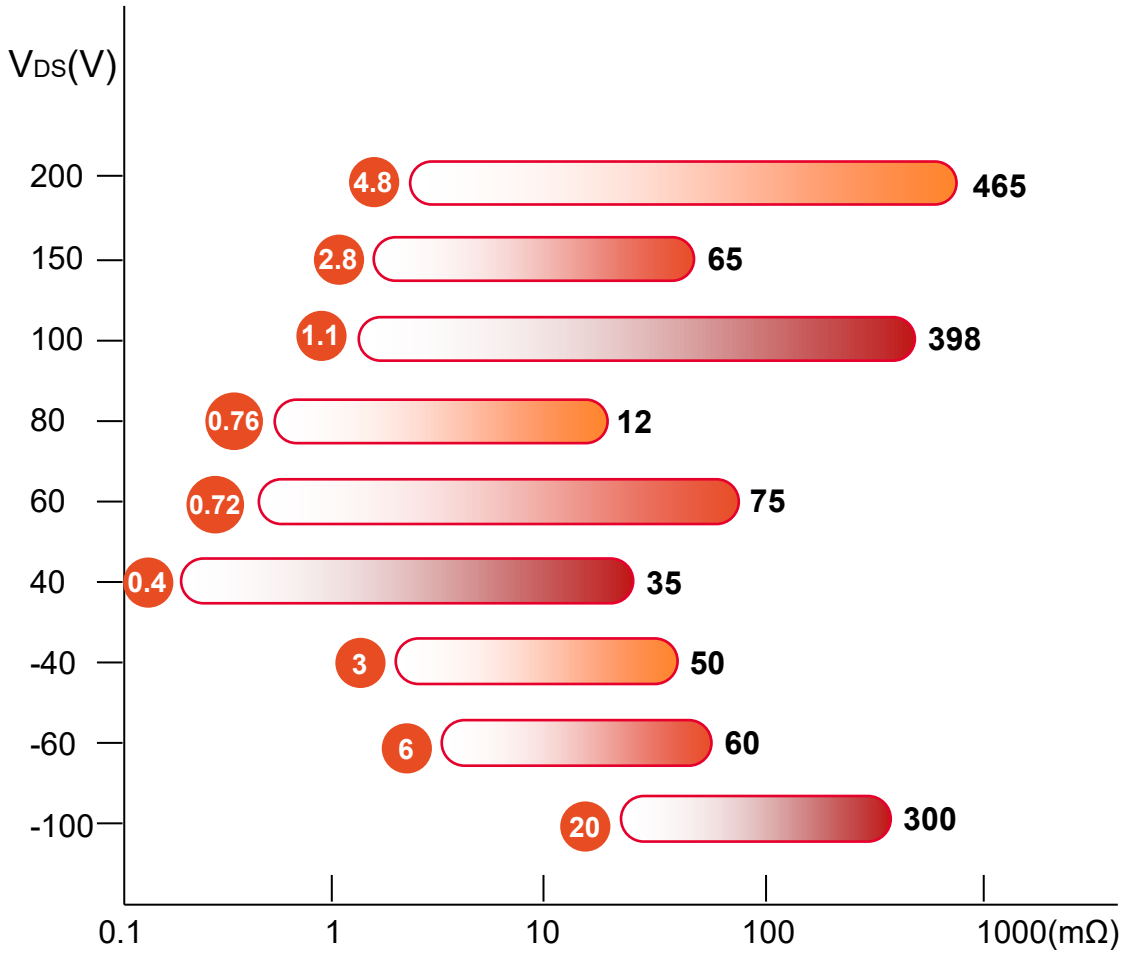
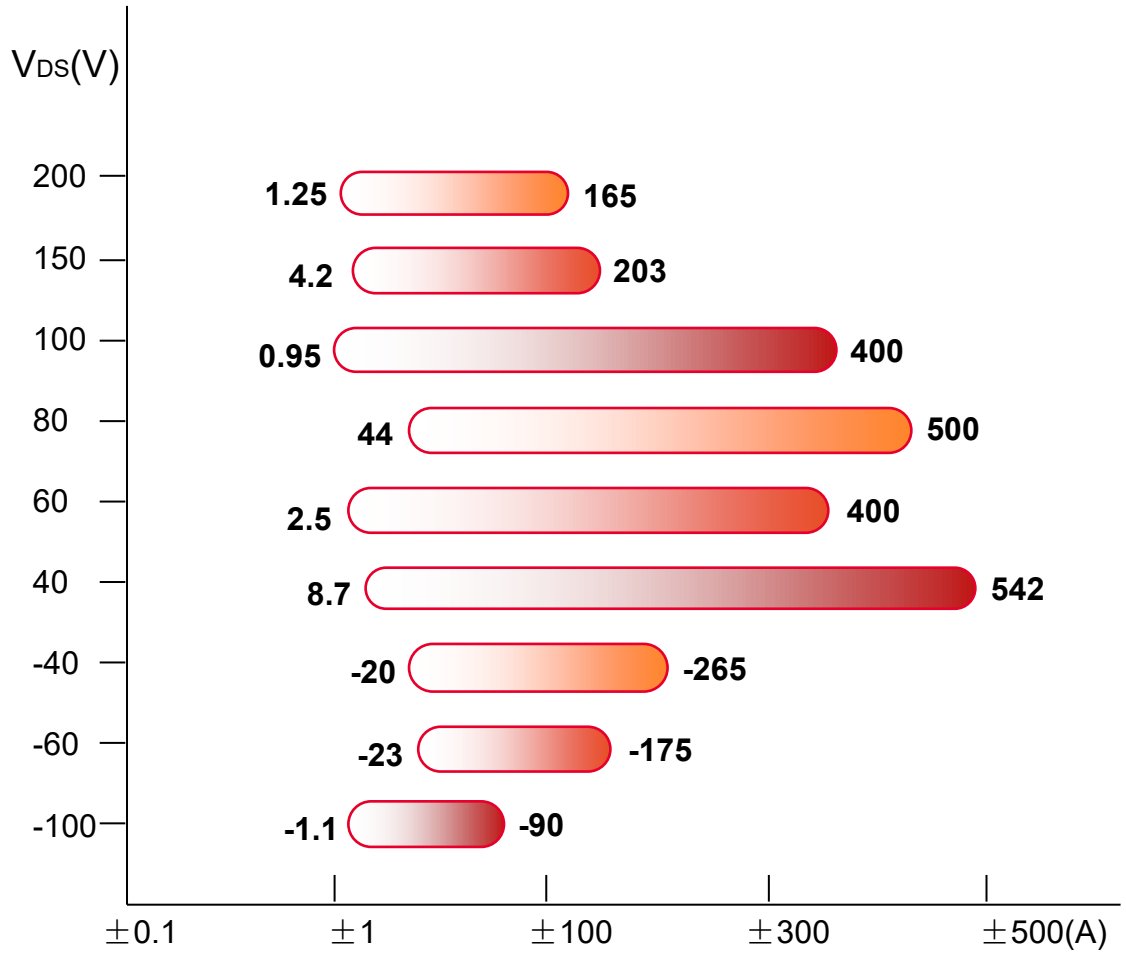
$R_{DS(ON)}$Max@VGS=10V



IDS@ TC=25° C



SJ MOSFET Product

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SJ MOSFET Product atlas

SJ MOS

◆ Mass Production

- G2

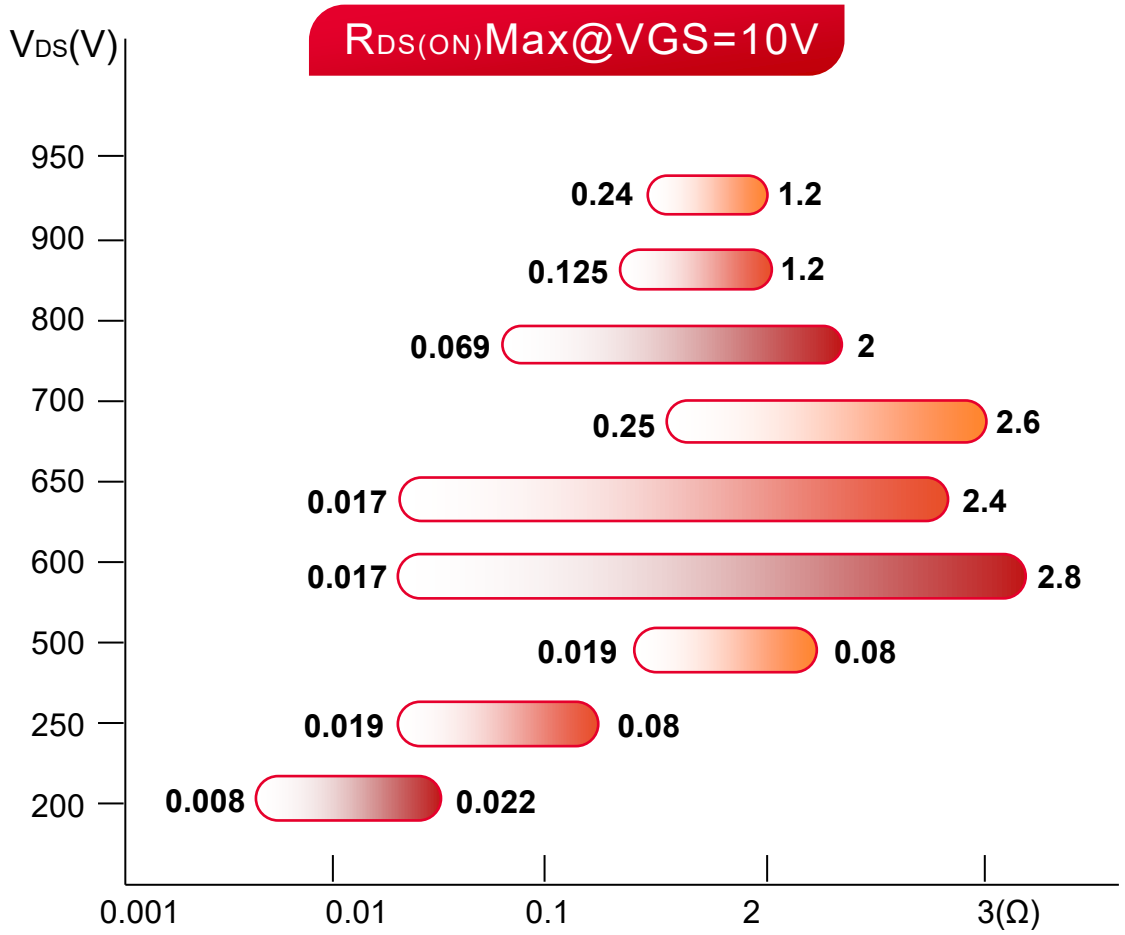
200V | 250V | 500V | 600V
650V | 700V | 800V | 900V
950V

◆ Under Developing

- G3

650V

SJ MOSFET Product range



Discrete Device and module products

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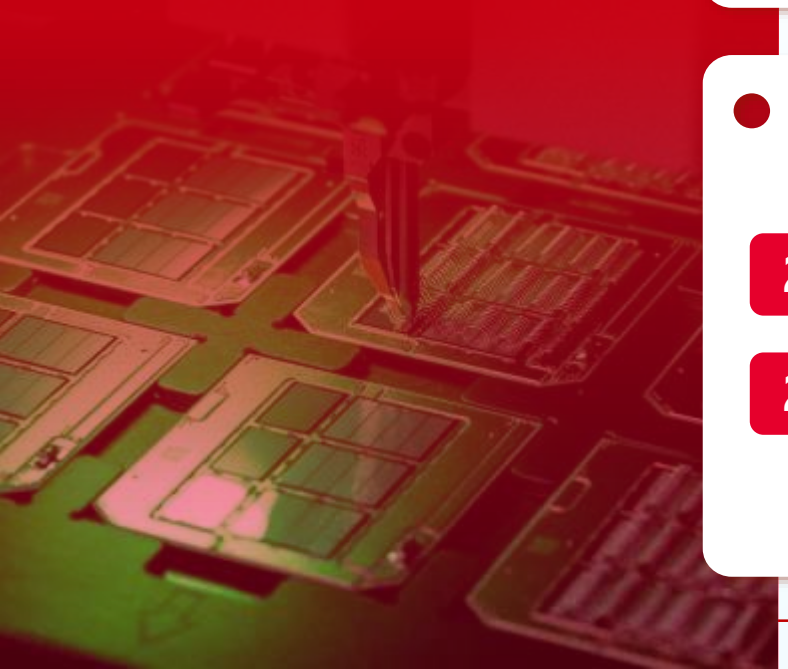
Power module related capability is unde planning.

Need customer provide product design details and requirements 8 months ahead.



Production

Discrete


TO220(3)/247(2)


DFN QFN


TO220(2)/247(3)


TO220N(2)


SAPKG-9L


TO252(2)


TO263(2)


TO247(4)


TO263(7)

Power Module (Molding)


SOT227

Development

Discrete

2025


TOLL

2026


SPAK-16L

Power Module(Molding)


SPAK-4L


SSC Module


SPAK-4L Plus


xPAK

Organizational Chart

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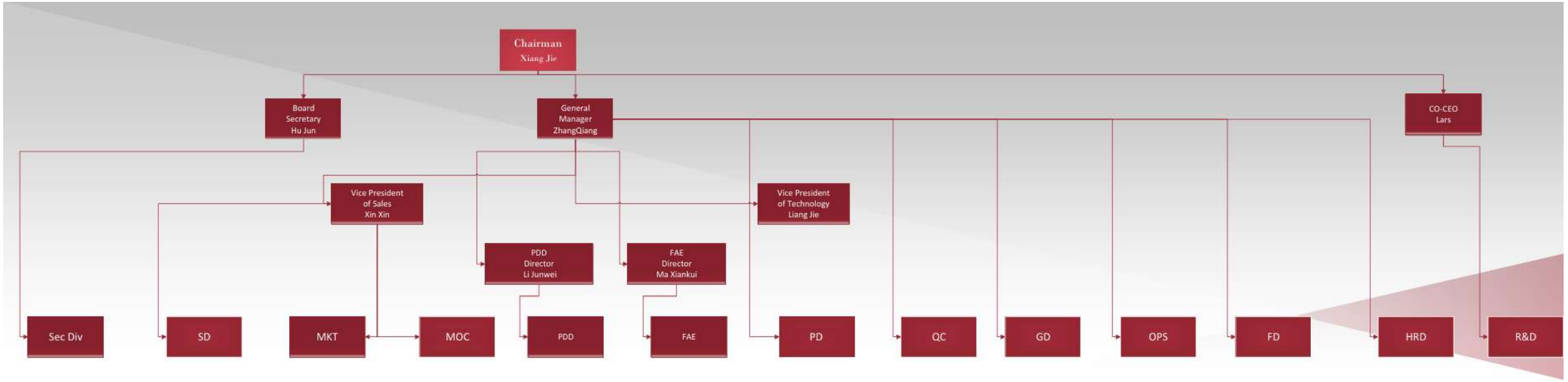

Technical team

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Technical R&D team

Composed of top technical experts from Europe and China in IGBT, SiC design and manufacturing, as well as industry leaders with excellent performance and decades of practical experience in the field of power semiconductors.

Co-CEO Lars

PhD, 33 academic papers
From 2014 to 2022, served as the head of SiC research and development at Hitachi Energy (formerly ABB Semiconductor, Switzerland)

Co-CEO Zhang qiang

From 2016 to 2019, Wuxi Sichuang Power Electronics
From 2009 to 2016, China CRRC Xi'an Yongdian

DIRECTOR Roland

From 2019 to 2025, CEO of Saijing Asia Pacific Semiconductor
From 2000 to 2018, ABB Semiconductor Company in Switzerland
Vice President, member of the senior management team

Technical team

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SwissSEM SCM and Quality(VP)

2002-2019
Head of Supply Chain and Quality Management, ABB Semiconductor, Switzerland

SwissSEM PM and Testing(VP)

36 academic papers and 12 patents
From 1996 to 2018, he was the Global Product Strategy Manager & Head of Product Development at ABB Semiconductor, Switzerland

SwissSEM VP

Ph.D., 25 academic papers, 6 patents
From 2008 to 2018, he was the head of the medium voltage device department of ABB Semiconductor Company in Switzerland

Deputy General Manager

It has 10 patents, 2 provincial and ministerial awards, and 1 municipal award
From 2015 to 2019, Wuxi Infineon served as the head of the field process of electric vehicle products

技术团队
Technical team

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SwissSEM Senior R&D Engineer

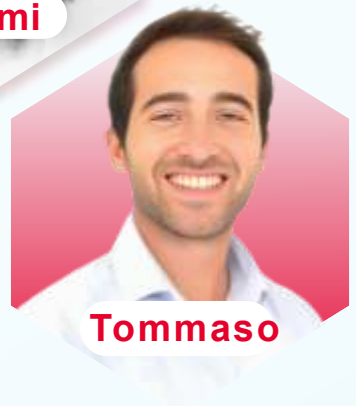
From 2019 to 2023, worked as a Senior R&D Engineer for IGBT&SiC power semiconductor devices at Hitachi Energy (formerly ABB Semiconductor, Switzerland)

SwissSEM Senior Process Engineer

From 2014 to 2022, worked as a Senior Process Engineer (Process and Quality Control, Industry 4.0 Manufacturing Intelligent Manufacturing) at Hitachi Energy (formerly ABB Semiconductors, Switzerland)

SwissSEM Senior R&D Engineer

2021-2023, Senior R&D Engineer for IGBT&SiC Power Semiconductor Devices at Hitachi Energy (formerly ABB Semiconductors Switzerland)



SwissSEM R&D Engineer Chip Design

PhD, 2 academic papers
Researcher at IBM Zurich Research Laboratory from 2014 to 2024

SwissSEM Senior Test Engineer

PhD, 33 academic papers
From 2014 to 2022, served as the head of SiC research and development at Hitachi Energy (formerly ABB Semiconductor, Switzerland)

Fully automated intelligent manufacturing

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Our product is produced in a 1000 level clean workshop throughout the entire process

Adopting fully automated intelligent manufacturing design and implementing extremely strict quality management standards, ensuring that every product has excellent electrical performance, consistency, and reliability.

Fully automated intelligent manufacturing

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- The most advanced and automated manufacturing equipment in the world, with no need for manual intervention in all process steps

- **Intelligent management system:**

  It includes components such as ERP, EAP, MES, and BI to jointly build an efficient and intelligent production environment.

  All process parameters, materials and accessories used for each product are traceable, and every process step and test result is monitored in real-time and intelligently.

- **Total Quality Control and Management System:**

AQG324

Vehicle grade power module standard

IATF16949

2016 Automotive Quality Management System

ISO9001、ISO14001、ISO45001

management system

RoHS2.0

EU Standard

UL

American certification

Advanced information management system

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The most advanced information management system in the entire industry

Strictly control product reliability and consistency through data from various stages. We can provide testing data for each product along with the shipment according to the customer's needs.

- The MES system is responsible for monitoring, managing, and optimizing various aspects of the production process, and using BI big data analysis systems to analyze large amounts of data in the production process, extract valuable information and data, in order to better understand business operations and discover trends.
- MES system can also manage the testing process in the production process, including product testing, quality inspection, etc. Real time collection and analysis of test data (SPC system analysis) is achieved through connection with testing equipment. During the testing process, the MES system can automatically determine the qualification of the product based on its testing results and quality standards, and record relevant data for subsequent traceability.

Comprehensive testing system

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We have the most comprehensive testing system in the industry, with complete and reliable testing data for new products

TEST	TEST PROJECT	TEST REQUIREMENTS	TEST CONDITION
HTS	High Temperature Storage	High-temperature storage	Ta = 150°C, t = 1000h
LTS	Low Temperature Storage	Low-temperature storage	Ta = -40°C, t = 1000h
HTRB	High Temperature Reverse Bias Test	High temperature reverse bias test	Ta = 150°C, t = 1000h, Vce = 80% Vcemax, Vge = 0V
HTGB	High Temperature Gate Bias Test	High temperature gate bias test	Ta = 150°C, t = 1000h, Vce = 0V, Vge = ± 20V
H3TRB	High Temperature High Humidity Test	High temperature and high humidity test	Ta = 85°C, t = 1000h, Vce = 80V, Vge = 0V, RH = 85%
TST	Thermal Shock Test	Thermal shock test	Tcmin = -40°C, Tcmax = 125°C, t_{storge} = 0.5h/0.5h, N_{cycles} = 1000cycles
PCsec	Powercycling sec. Test	Power cycle second-level test	ton < 5s, IL > 85%I_{norm} Termination conditions: VCEsat / VF ≥ 5%; Rth ≥ 20%
PCmin	Powercycling min. Test	Power cycle minute-level testing	ton > 15s, IL > 85%I_{norm} Termination conditions: VCEsat / VF ≥ 5%; Rth ≥ 20%

IGBT chip and diode chip products

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i20/i21 IGBT Chip features:

- Advanced trench gate technology, low saturation drop Vce(sat) and low switching loss (Eon+Eoff)
- Optimized the design of the N-enhancement layer
- The i21 IGBT chip is optimized for high stray inductance (Ls) applications

i23 IGBT Chip features:

- Micro-fine trench gate IGBT technology for ultra-low loss Eon+Eoff
- Controllability of soft shutdown and turn-on with Rg for a wide range of applications
- High Short Circuit Capability (ISC)
- Local Carrier Limit Control (LC3)

Sunking is based on application requirements with the goal of high quality and high reliability, the i20/i21/i23 series of IGBT chips have been developed

Model	series	Vces(V)	IC(A)	ICM(A)	Vce(sat) @125°C	Max. Dies Per Wafer	size (mm*mm)	thickness (μm)
SIS0100C120i20	i20	1200	100	200	2.05	784	8.8×8.8	135
SIS0150C120i20	i20	1200	150	300	2.05	547	10.5×10.5	135
SIS0200C120i20	i20	1200	200	400	2.05	420	11.9×11.9	135
SIS0250C120i20	i20	1200	250	500	1.95	126(8')/315(12')	15.7×12.1	135
SIS0075C175i20	i20	1700	75	150	1.85	320	8.9×8.9	185
SIS0100C175i20	i20	1700	100	200	1.85	247	10.1×10.1	185
SIS0150C175i20	i20	1700	150	300	1.85	166	12.1×12.1	185
SIS0200C175i20	i20	1700	200	400	1.85	126	15.8×12.1	185
SIS0200C120i21	i21	1200	200	400	1.68	386	15.8×12.1	145

Model	series	Vces(V)	IC(A)	ICM(A)	Vce(sat)@125°C	Max. Dies Per Wafer	size (mm*mm)	thickness (μm)
SIS0150C105i23	i23	1050	150	300	1.95	765	9×9.8	100
SIS0150C120i23	i23	1200	150	300	1.7	597	10×10.1	135
SIS0200C120i23	i23	1200	200	400	1.7	454	11.5×11.5	135
SIS0300C120i23	i23	1200	300	600	1.7	315	15.7×12.1	135
SIS0300C170i23	i23	1700	300	600	1.95	290	16.4×12.4	175

IGBT chip and diode chip products

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Based on application requirements, Saijing has developed a series of diode chips with high quality and high reliability as the goal

d20 Diode chip characteristics

- Low Forward Conduction Drop VF and Low Reverse Recovery Loss (Erec)
- Advanced emitter efficiency design
- positive temperature coefficient

Model	series	VRRM(V)	IF(A)	VF(V)@125°C	Max. Dies Per Wafer	size (mm*mm)	thickness (μm)
SID0075C120d20	d20	1200	75	1.90	1741	6.0×6.0	130
SID0100C120d20	d20	1200	100	1.90	1363	6.8×6.7	130
SID0150C120d20	d20	1200	150	1.90	955	8.1×8.0	130
SID0250C120d20	d20	1200	250	2.15	236(8')/594(12')	8.5×12.1	130
SID0075C175d20	d20	1700	75	1.85	579	6.7×6.7	130
SID0100C175d20	d20	1700	100	1.85	453	7.6×7.6	130
SID0150C175d20	d20	1700	150	1.85	314	8.5×9.5	130
SID0200C175d20	d20	1700	200	1.85	236	8.5×12.1	185

d23 Diode chip characteristics

- 1200V/1700V Quasi-Local Lifetime Control (QLLC)
- Ultra-low forward voltage drop VF and low reverse recovery loss EREC while maintaining soft reverse recovery characteristics
- Neutral temperature coefficient

Model	series	VRRM(V)	IF(A)	VF(V)@125°C	Max. Dies Per Wafer	size (mm*mm)	thickness (μm)
SID0100C105d23	d23	1050	100	2.1	2227	5.3×5.3	100
SID0300C120d23	d23	1200	300	1.9	236	8.47×12.07	130
SID0340C120d23	d23	1200	340	1.75	214	9.19×12.47	130
SID0300C175d23	d23	1700	300	2.15	220	8.9×12.4	175

SiC chip products - target specifications

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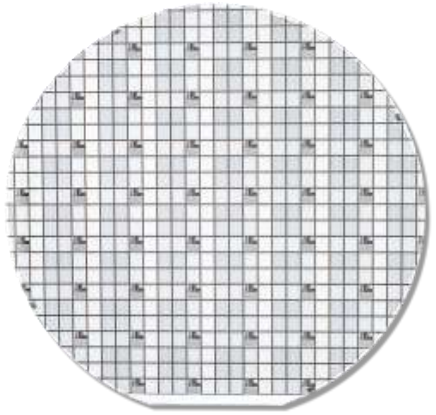

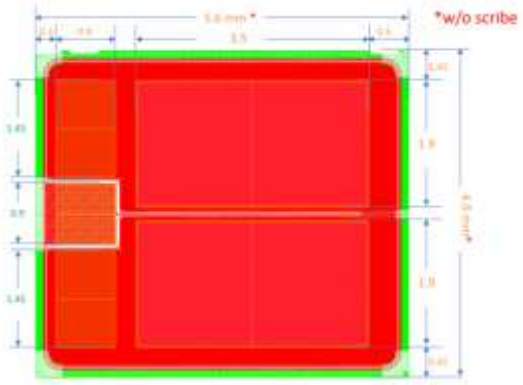

SiC Chip parameters

Model	series	size(mm*mm)	Rds,on (mΩ)@25℃/175℃	Short-circuit pulse tpsc(μs)@125℃	thickness (μm)	of each wafer Maximum number of chips
SC0012C120m24	m24	5.0 x 5.7	12/20	2	180	470
SC0013C120m23	m23	5.0 x 5.7	13/24	3	180	470
SC0015C140m23	m23	5.0 x 5.7	15/28	3	180	470

SiC Chip features

- Performance surpasses that of third-generation SiC MOSFET technology
- The top is metallized for bonding or DTS
- Static performance matches the performance requirements of advanced automotive MOSFET products
- Dynamic switching performance is suitable for applications in EVD and HEEV modules
- High reliability and high robustness
  - Satisfy AEC-Q101 request
  - SCSOA, HTRB & H3TRB

SiC chip products - switch characteristics

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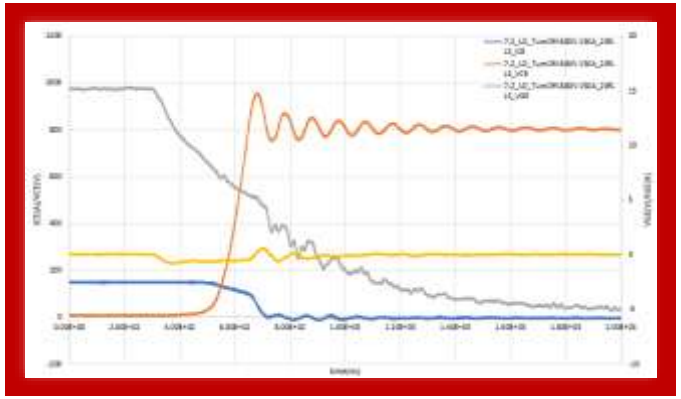
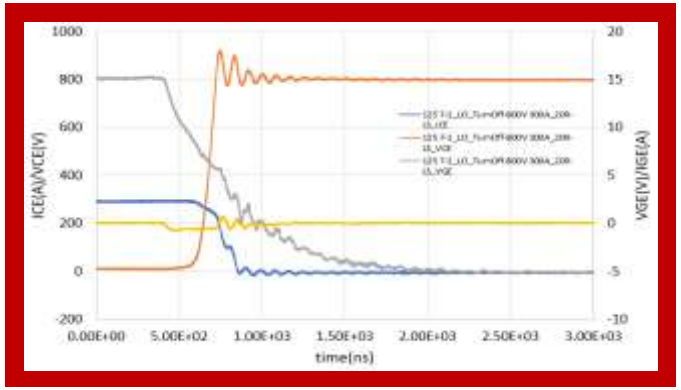
Dynamic characteristics 25℃ waveform

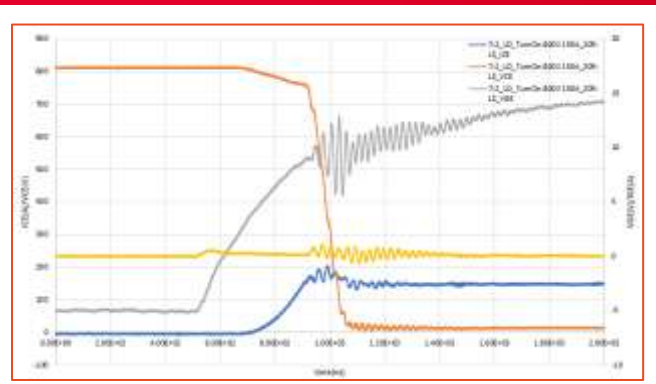
Turn-off



Turn-off ID >300A @ 800V, 125°C



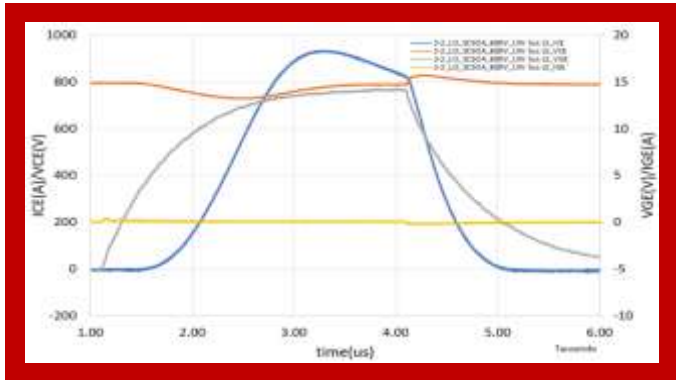
Turn-on

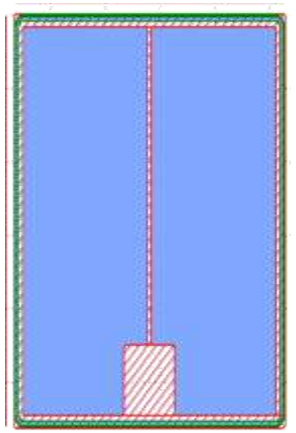


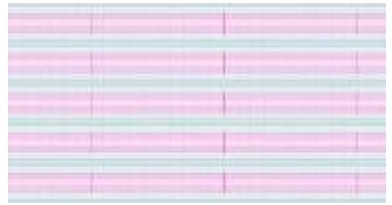
- The controllable rate of current change and rate of voltage change pass through the gate resistor
- The gate running line layout features no oscillation and fast switching
- Body diode operation and MOS control
- A large area of bonding area

Short circuit and reverse blocking of the safe work area

Up to 3us short-circuit safe working area at 800V







SiC Chip Products - Performance Comparison

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* measured		Competitor 1 (5.0 x 5.0 mm2)		Competitor 2 (5.6 x 4.9 mm2)		Competitor 3 (~4.5 x 4.5 mm2)		SSEM specification (5.7 x 5.0 mm2)	
Leakage source breakdown voltage	VDSS (V)	1200 ID<30mA		1200 ID<1mA		1200 ID<0.1mA		**>1500*** **ID<1mA**	
Continuous drain current	ID (A)	122 VG=+18V, R_{th}^{j-c}=0.31K/W		160 VG=+18V, R_{th}^{j-c}=0.19K/W		89 VG=+18V, R_{th}^{j-c}=0.43K/W		**140** **VG=+18V**	
gate source voltage range	VGmin.. (V) VGmax.. (V)	-2 +21		-5 +18		-3 +18		**-10** **+20**	
Gate threshold voltage	VTH (V)	2.8 - 4.8 (3.8) ID=36mA		2 - 4.2 (3.1) ID=10mA		2.0 - 4.4 (2.7) ID=20mA		**2 - 3 (3*)** **ID=10mA**	
Static leakage resistance at room temperature and 175°C	RDS,on (mOhm)	11 / 23 ID=68A, VG=+18V		13.5 / 24 ID=100A, VG=+18V		22 ID=40A, VG=+18V		**(13-15) / (20-22)** **ID=100A, VG=+18V**	
Diode forward voltage	VSD (V)	3.3 ISD=68A		4.9 ISD=80A		4.5 ISD=40A		**5.0** **ISD=100A**	
Gate input resistor	RGint (Ohm)	4		1*		1.5		**2-3**	
Warmth	°C	175		200		175		**175**	
Short-circuit capability	us	<1.5		-				**2-3**	
Opening loss	VDS=800V VGmin..VG max	Eon (uJ)	842	RG=0Ohm ID=68A	1336	RG=2.2Ohm ID=80A	1212	RG=4.5Ohm ID=40A	**<1400**	**RG=1Ohm** **ID=100A**
Shutdown and loss		Eoff (uJ)	635		608		307		**<700**	

Core components of the new energy industry chain

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Energy storage

Other power generation

Flexible and conventional UHV DC transmission

Flexible DC and flexible low-frequency power transmission

Rail transit vehicles

Residential and commercial electricity

Electric vehicle

Energy storage

Industrial control

Photovoltaic power generation

Onshore and offshore power generation

合作伙伴
partner

Saijing is deeply involved in the field of power electronics, has accumulated rich customer resources and industry experience, and has long-term cooperation with customers for mutual benefit and win-win results with excellent products and services

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Thanks for listening

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Looking forward to cooperation

public platform

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